

AOS Semiconductor Product Reliability Report

AO4407 / AO4407L, rev D

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

495 Mercury Drive Sunnyvale, CA 94085 U.S.

Tel: (408) 830-9742

www.aosmd.com

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This AOS product reliability report summarizes the qualification result for AO4407. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4407 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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I. Product Description:

The AO4407 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications. Standard Product AO4407 is Pb-free (meets ROHS & Sony 259 specifications). AO4407L is a Green Product ordering option. AO4407 and AO4407L are electrically identical.

Absolute Maximum F	Ratings T,	₄=25°C unless	otherwise noted		
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage	-	V _{GS}	±25	V	
Continuous Drain	T _A =25°C		-12		
Current	T _A =70°C	I _D	-10	А	
Pulsed Drain Current		I _{DM}	-60		
	T _A =25°C	Pn	3	w	
Power Dissipation	T _A =70°C	I D	2.1	vv	
Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C	

Thermal Characteristics						
Parameter		Symbol	Тур	Max	Units	
Maximum Junction-to- Ambient	T ≤ 10s		28	40	°C/W	
Maximum Junction-to- Ambient	Steady- State	- R _{θJA}	54	75	°C/W	
Maximum Junction-to-Lead	Steady- State	$R_{ ext{ heta}JL}$	21	30	°C/W	



II. Die / Package Information:

	AO4407	AO4407L (Green Compound)
Process	Standard sub-micron low voltage P channel process	Standard sub-micron low voltage P channel process
Package Type Lead Frame Die Attach Bond wire Mold Material Filler % (Spherical/Flake) Flammability Rating Backside Metallization Moisture Level	8 leads SOIC Ag with Solder Plate Silver-filled Epoxy 2 mils Au wire Epoxy resin with silica filler 90/10 UL-94 V-0 Ti / Ni / Ag Up to Level 1 *	8 leads SOIC Ag with Solder Plate Silver-filled Epoxy 2 mils Au wire Epoxy resin with silica filler 100/0 UL-94 V-0 Ti / Ni / Ag Up to Level 1*

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO4407 (Standard) & AO4407L (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	Standard: 1hrPCT+3 cycle reflow@260°c Green: 168hr 85°c /85%RH +3 cycle reflow@260°c	Ohr	Standard: 6 lots Green: 16 lots	3300 pcs	0
HTGB	Temp = 150°C, Vgs=100% of Vgsmax	168 / 500 hrs 1000 hrs	6 lots (Note A*)	492 pcs 77+5 pcs / lot	0
HTRB	Temp = 150°C, Vds=80% of Vdsmax	168 / 500 hrs 1000 hrs	6 lots (Note A*)	492 pcs 77+5 pcs / lot	0
HAST	130 +/- 2°C, 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard: 6 lots Green: 13 lots (Note B**)	1045 pcs 50+5 pcs / lot	0
Pressure Pot	121°C, 15+/-1 PSIG, RH=100%	96 hrs	Standard: 5 lots Green: 16 lots (Note B**)	1155 pcs 50+5 pcs / lot	0
Temperature Cycle	-65°C to 150°C, air to air, 0.5hr per cycle	250 / 500 cycles	Standard: 5 lots Green: 15 lots (Note B**)	1100 pcs 50+5 pcs / lot	0



Continues					
DPA	Internal Vision	NA	5	5	0
	Cross-section		5	5	
	X-ray		5	5	
	-				
CSAM		NA	5	5	0
			-	-	-
Bond	Room Temp	0hr	40	40 wires	0
Integrity	150°C bake	250hr	40	40 wires	
	150°C bake	500hr	40	40 wires	
Solderability	230°C	5 sec	15	15 leads	0
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Die Shear	150°C	0hr	10	10	0

III. Result of Reliability Stress for AO4407 (Standard) & AO4407L (Green) Continues

Note A: The HTGB and HTRB reliability data presents total of available AO4407 and AO4407L burn-in data up to the published date.

Note B: The pressure pot, temperature cycle and HAST reliability data for AO4407 and AO4407L comes from the AOS generic package qualification data.

IV. Reliability Evaluation FIT rate (per billion): 7 MTTF =16307 years

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO3401). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $Chi^2 \times 10^9 / [2 (N) (H) (Af)]$ = 1.83 × 10⁹ / [2 (3×164) (168) (258) + 2 (164) (500)(258) + 2 (2×164) (1000) (258)] = 7 MTTF = $10^9 / FIT = 1.42 \times 10^8 hrs = 16307$ years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = $55^{\circ}C$) Acceleration Factor [Af] = Exp [Ea / k (1/Tju - 1/Tjs)] Acceleration Factor ratio list:

7.00010141							
	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

 \mathbf{k} = Boltzmann's constant, 8.617164 X 10⁻⁵ e V / K



V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual. Guaranteed Outgoing Defect Rate: **< 25 ppm** Quality Sample Plan: conform to **Mil-Std-105D**